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作者: Goodnick, SM (Goodnick, Stephen M.); Saraniti, M (Saraniti, Marco)
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地址: [Goodnick, Stephen M.; Saraniti, Marco] Arizona State Univ, Sch Elect Comp & Energy, Tempe, AZ 85287 USA
通讯作者地址: Goodnick, SM (通讯作者),Arizona State Univ, Sch Elect Comp & Energy, Tempe, AZ 85287 USA.
电子邮件地址: stephen.goodnick@asu.edu
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